

C1 β' (ind.)
an upper electrode formed above the lower electrode via the capacitor dielectric film,
a grain boundary between adjacent two of said plurality of crystal grains constituting the
lower electrode being substantially perpendicular to an interface between the lower electrode and
the capacitor insulating film.

β'
19. (Amended) A semiconductor device comprising:
a semiconductor substrate;
a conductive plug formed on the semiconductor substrate;
a lower electrode formed in contact with the conductive plug and having a side and upper
surface, a surface area of the side being larger than a surface area of the upper surface;
a capacitor insulating film formed on a side of the lower electrode; and
an upper electrode formed above the lower electrode via the capacitor insulating film,
the capacitor insulating film being formed above a top surface of the lower electrode via
a second insulating film different from the capacitor insulating film.

REMARKS

In this Amendment, Applicants have amended claims 10 and 19 to more appropriately
define the invention. In accordance with the requirements of 37 C.F.R. § 1.121(c)(1), Applicants
provide a marked-up version of the amended claims in an attached Appendix designated
"Version of Claims with Markings to Show Changes Made." Claims 10, 14, 15, 19, and 24
remain pending.

In the September 13, 2001 Office Action, the Examiner objected to claims 10 and 19
because of informalities; rejected claim 19 under 35 U.S.C. § 102(b) as anticipated by Kashihara
et al. (U.S. Patent No. 5,567,964); rejected claims 10, 14, 19, and 24 under 35 U.S.C. § 102(b) as